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(54) Title: DRYING HIGH ASPECT RATIO FEATURES

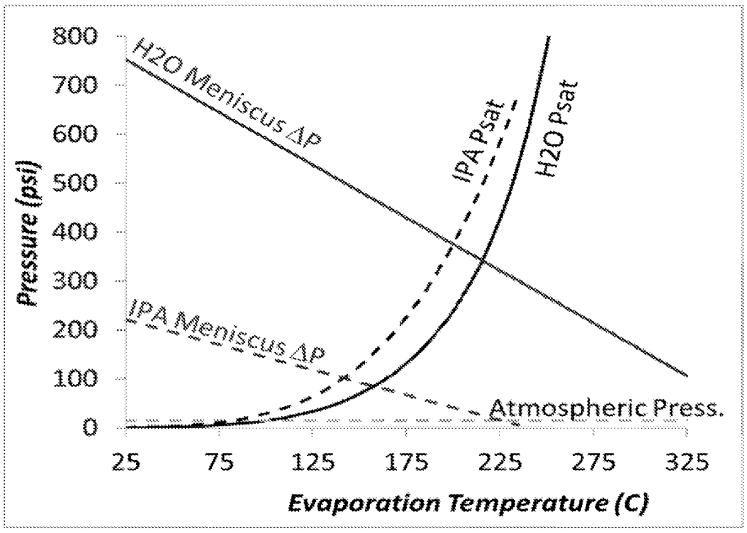

FIG. 5

(57) Abstract: Methods of drying a semiconductor substrate may include applying a drying agent to a semiconductor substrate, where the drying agent wets the semiconductor substrate. The methods may include heating a chamber housing the semiconductor substrate to a temperature above an atmospheric pressure boiling point of the drying agent until a vapor-liquid equilibrium of the drying agent within the chamber has been reached. The methods may further include venting the chamber, where the venting vaporizes the liquid phase of the drying agent from the semiconductor substrate.

WO 2018/094084 A1

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